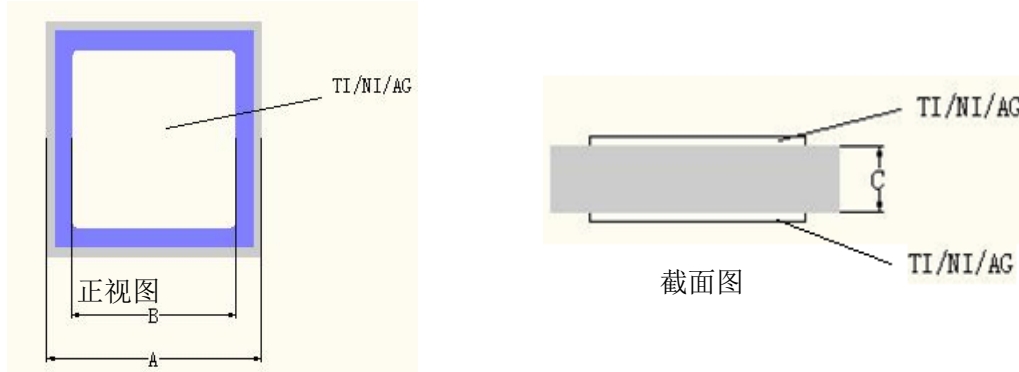


一、芯片特征：

1. 平面工艺
2. 超低反向漏电流
3. 芯片表面两面蒸镀Ti/Ni/Ag

二、芯片结构



三、产品型号及规格：

1. 200W

Part Number		Dice Scale (A)	Scale (B)	Scale (C)	Reverse stand-off Voltage	Breakdown voltage		Test Current	Reverse Leakage		Max Clamp Voltage	Peak Pulse Current
						VBR@IT			IR@VRWM			
					VRWM	Min	Max	IT	UNI	BI	Vc@Ipp	Ipp
UNI	BI	mil	mil	um	V	V	V	mA	uA	uA	V	A
SMFJ5.0A	SMFJ5.0CA	47±2	35±1	320±20	5.0	6.40	7.07	10	100	100	9.2	21.7
SMFJ6.0A	SMFJ6.0CA	47±2	35±1	320±20	6.0	6.67	7.37	10	100	100	10.3	19.4
/	SMFJ6.5CA	47±2	35±1	320±20	6.5	7.22	7.98	10	100	100	11.2	17.9
P2KE6.8A	P2KE6.8CA	47±2	35±1	320±20	5.8	6.45	7.14	10	100	100	10.5	19.0
/	P2KE7.5CA	47±2	35±1	320±20	6.4	7.13	7.88	10	100	100	11.3	17.6

2. 400W

Part Number		Dice Scale (A)	Scale (B)	Scale (C)	Reverse stand-off Voltage	Breakdown voltage		Test Current	Reverse Leakage		Max Clamp Voltage	Peak Pulse Current
						VBR@IT			IR@VRWM			
						VRWM	Min	Max	IT	UNI	BI	Vc@Ipp
UNI	BI	UNI/BI	UNI/BI	um	V	V	V	mA	uA	uA	V	A
SMAJ5. 0A	SMAJ5. 0CA	60±2/70±2	48±1/58±1	320±20	5. 0	6. 40	7. 07	10	100	100	9. 2	43. 5
SMAJ6. 0A	SMAJ6. 0CA	60±2/70±2	48±1/58±1	320±20	6. 0	6. 67	7. 37	10	100	100	10. 3	38. 8
/	SMAJ6. 5CA	60±2	48±1	320±20	6. 5	7. 22	7. 98	10	100	100	11. 2	35. 7
P4KE6. 8A	P4KE6. 8CA	60±2/70±2	48±1/58±1	320±20	5. 8	6. 45	7. 14	10	100	100	10. 5	38. 1
/	P4KE7. 5CA	60±2	48±1	320±20	6. 4	7. 13	7. 88	10	100	100	11. 3	36. 3

3. 600W												
Part Number		Dice Scale (A)	Scale (B)	Scale (C)	Reverse stand-off Voltage	Breakdown voltage		Test Current	Reverse Leakage		Max Clamp Voltage	Peak Pulse Current
						VBR@IT			IR@VRWM			
						VRWM	Min	Max	IT	UNI	BI	
UNI	BI	mil	mil	um	V	V	V	mA	uA	uA	V	A
SMBJ5. 0A	SMBJ5. 0CA	79±2	64±1	320±20	5. 0	6. 40	7. 07	10	100	100	9. 2	65. 2
SMBJ6. 0A	SMBJ6. 0CA	79±2	64±1	320±20	6. 0	6. 67	7. 37	10	100	100	10. 3	58. 3
/	SMBJ6. 5CA	79±2	64±1	320±20	6. 5	7. 22	7. 98	10	100	100	11. 2	53. 6
P6KE6. 8A	P6KE6. 8CA	79±2	64±1	320±20	5. 8	6. 45	7. 14	10	100	100	10. 5	57. 1
/	P6KE7. 5CA	79±2	64±1	320±20	6. 4	7. 13	7. 88	10	100	100	11. 3	54. 0